



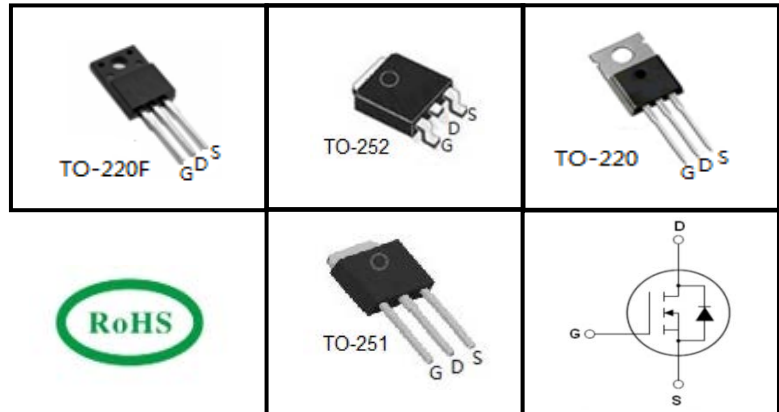
700V Super-Junction Power MOSFET

FEATURES

- Very low FOM $R_{DS(on)} \times Q_g$
- 100% avalanche tested
- RoHS compliant

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information				
Device	TPA70R360M	TPD70R360M	TPP70R360M	TPU70R360M
Package	TO-220F	TO-252	TO-220	TO-251
Marking	70R360M	70R360M	70R360M	70R360M

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted				
Parameter	Symbol	Value		Unit
		TO-252,TO-220,TO-251	TO-220F	
Drain-Source Voltage ($V_{GS} = 0\text{V}$)	V_{DSS}	700		V
Continuous Drain Current	I_D	$T_C = 25^\circ\text{C}$	11	A
		$T_C = 100^\circ\text{C}$	6.6	
Pulsed Drain Current (note1)	I_{DM}	33		A
Gate-Source Voltage	V_{GSS}	± 30		V
Single Pulse Avalanche Energy (note2)	E_{AS}	215		mJ
Avalanche Current (note1)	I_{AR}	1.8		A
Repetitive Avalanche Energy (note1)	E_{AR}	0.32		mJ
MOSFET dv/dt ruggedness, $V_{DS} = 0 \dots 480\text{V}$	dv/dt	50		V/ns
Reverse diode dv/dt, $V_{DS} = 0 \dots 480\text{V}$, $I_{SD} \leq I_D$	dv/dt	15		V/ns
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	83	31	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150		$^\circ\text{C}$

Thermal Resistance				
Parameter	Symbol	Value		Unit
		TO-252,TO-220,TO-251	TO-220F	
Thermal Resistance, Junction-to-Case	R_{thJC}	1.5	4	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62	80	



Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	700	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 700V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	μA
		$V_{DS} = 700V, V_{GS} = 0V, T_J = 150^\circ\text{C}$	--	--	100	
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30V$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.5	--	4.5	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 5.5A$	--	0.31	0.36	Ω
Gate resistance	R_G	$f = 1.0\text{MHz}$ open drain	--	18	--	Ω
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = 100V,$ $f = 1.0\text{MHz}$	--	871	--	μF
Output Capacitance	C_{oss}		--	37	--	
Reverse Transfer Capacitance	C_{rss}		--	5	--	
Total Gate Charge	Q_g	$V_{DD} = 520V, I_D = 11A,$ $V_{GS} = 10V$	--	22	--	nC
Gate-Source Charge	Q_{gs}		--	4	--	
Gate-Drain Charge	Q_{gd}		--	8	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 400V, I_D = 11A,$ $R_G = 25\Omega$	--	69.7	--	ns
Turn-on Rise Time	t_r		--	69.5	--	
Turn-off Delay Time	$t_{d(off)}$		--	145	--	
Turn-off Fall Time	t_f		--	59	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	$T_C = 25^\circ\text{C}$	--	--	11	A
Pulsed Diode Forward Current	I_{SM}		--	--	33	
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{SD} = 11A, V_{GS} = 0V$	--	0.9	1.2	V
Reverse Recovery Time	t_{rr}	$V_R = 400V, I_F = I_S,$ $di_F/dt = 100A/\mu s$	--	377	--	ns
Reverse Recovery Charge	Q_{rr}		--	3.4	--	μC
Peak Reverse Recovery Current	I_{rrm}		--	17.8	--	A

Notes

1. Repetitive Rating: Pulse Width limited by maximum junction temperature
2. $I_{AS} = 1.8A, V_{DD} = 50V, R_G = 25\Omega,$ Starting $T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse Width $\leq 300\mu s,$ Duty Cycle $\leq 1\%$



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

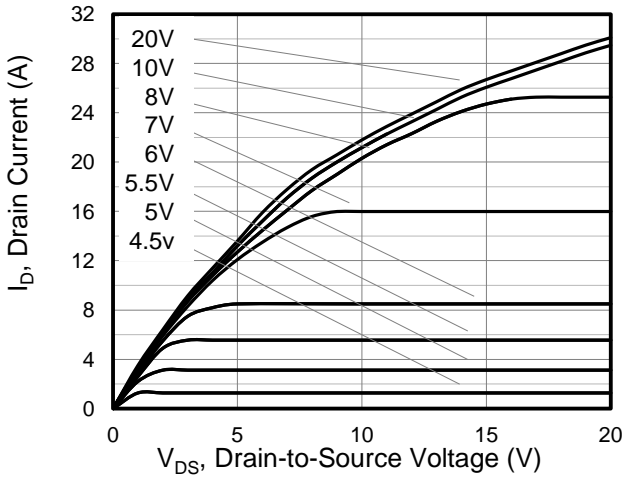


Figure 2. Transfer Characteristics

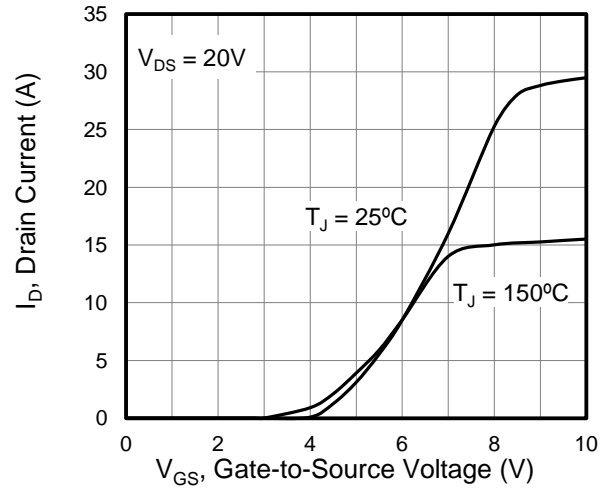


Figure 3. On-Resistance vs. Drain Current

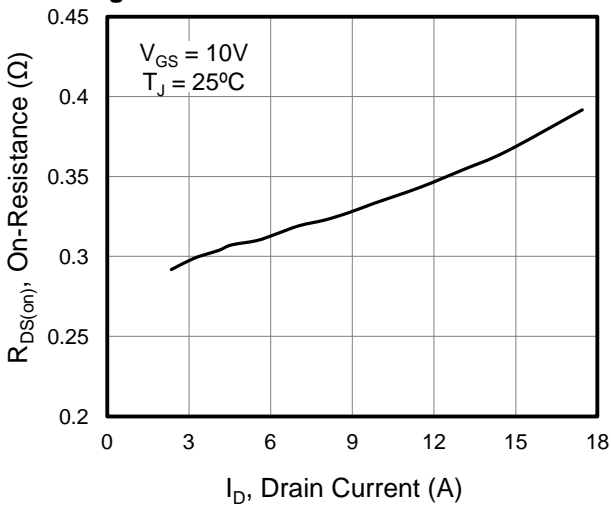


Figure 4. Capacitance

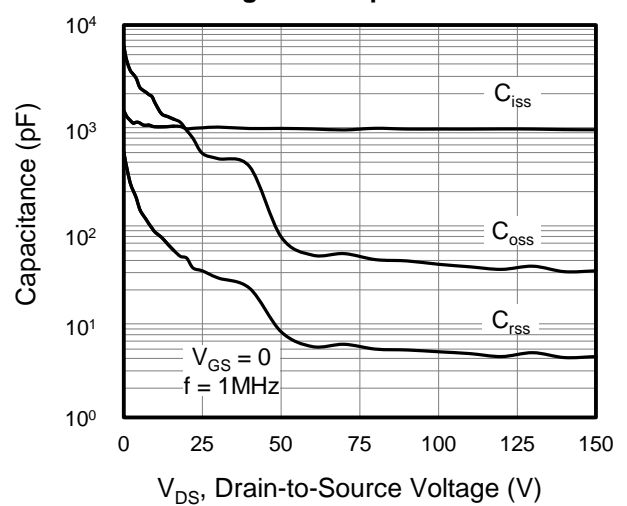


Figure 5. Gate Charge

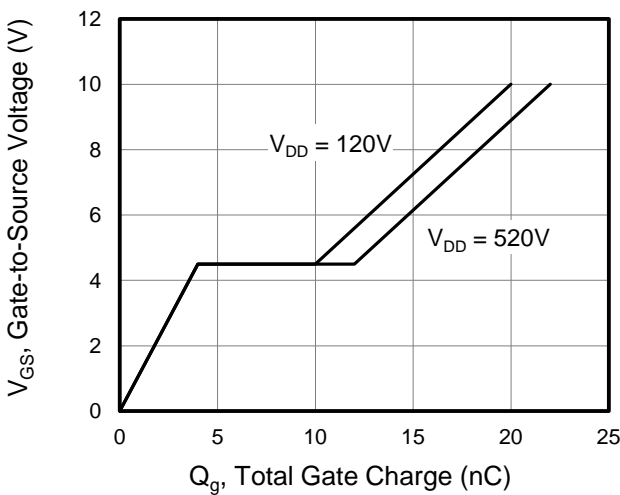
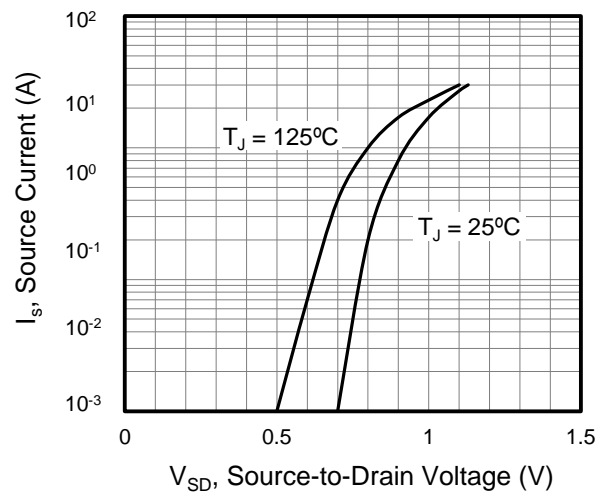


Figure 6. Body Diode Forward Voltage





Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. On-Resistance vs. Junction Temperature

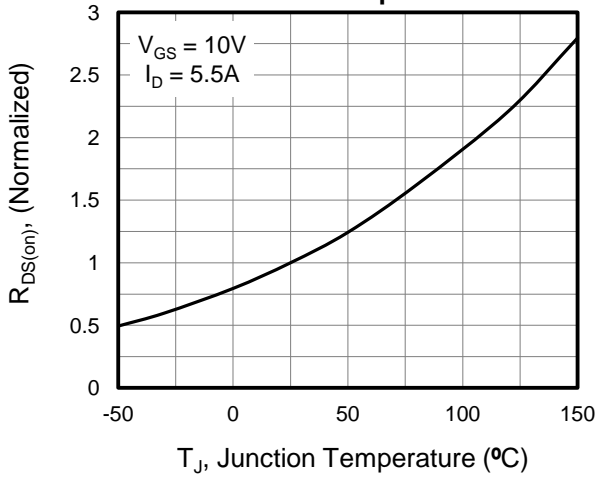


Figure 8. Breakdown voltage vs. Junction Temperature

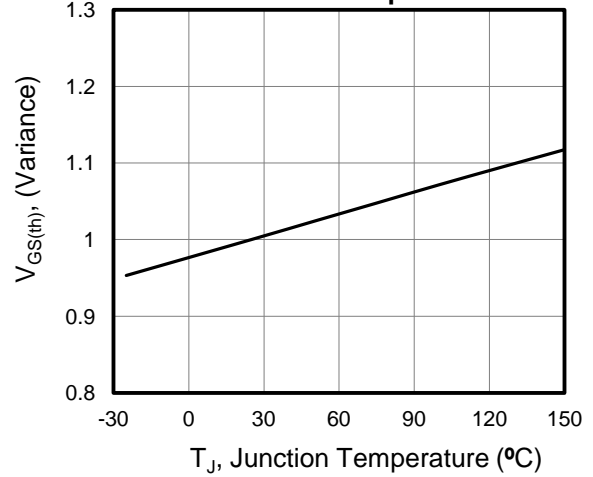


Figure 9. Transient Thermal Impedance TO-252/TO-220/TO-251

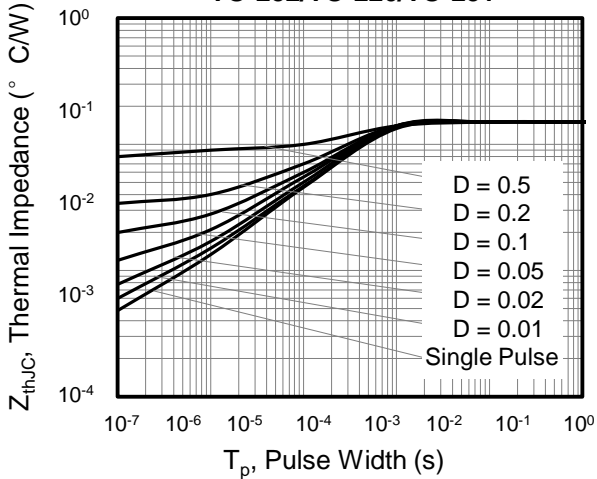


Figure 10. Transient Thermal Impedance TO-220F

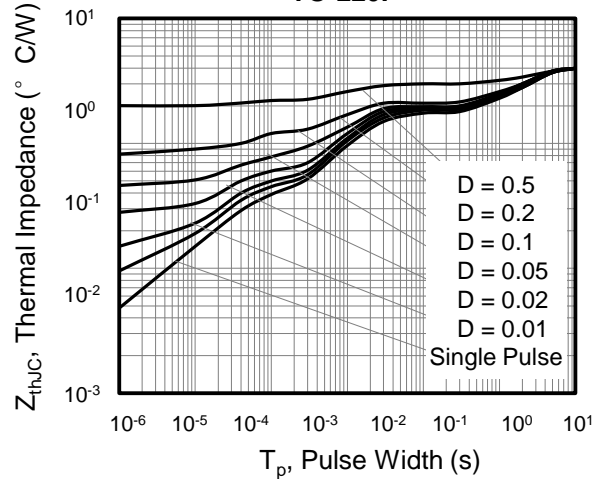


Figure 11. Safe operation area for TO-252/TO-220/TO-251

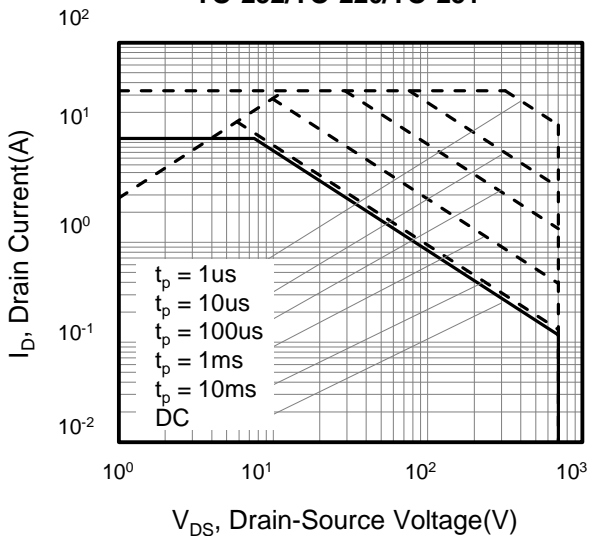


Figure 12. Safe operation area for TO-220F

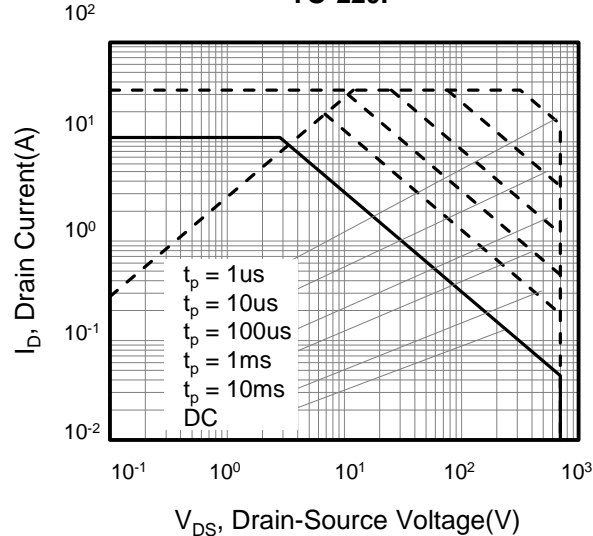




Figure A: Gate Charge Test Circuit and Waveform



Figure B: Resistive Switching Test Circuit and Waveform

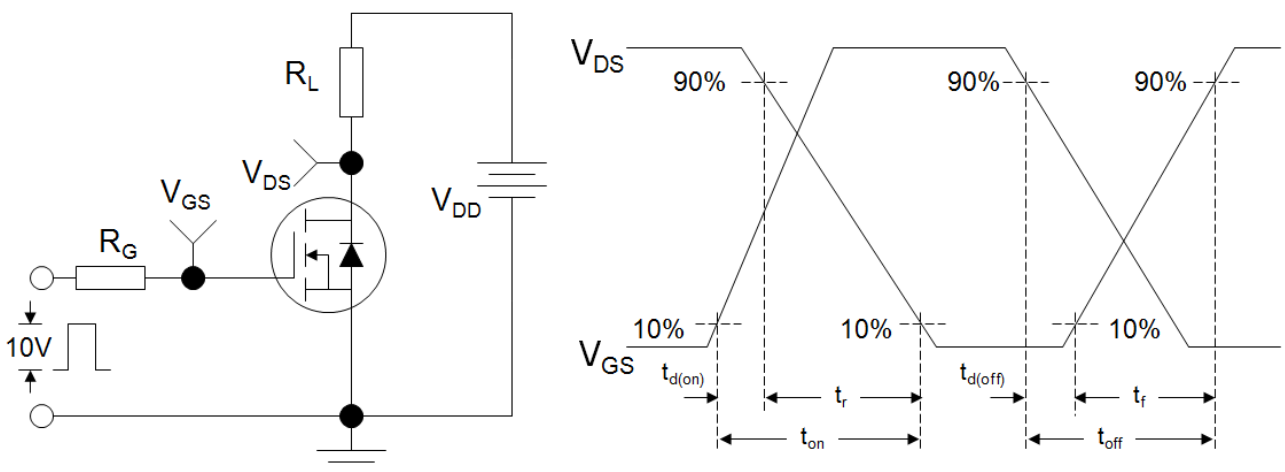
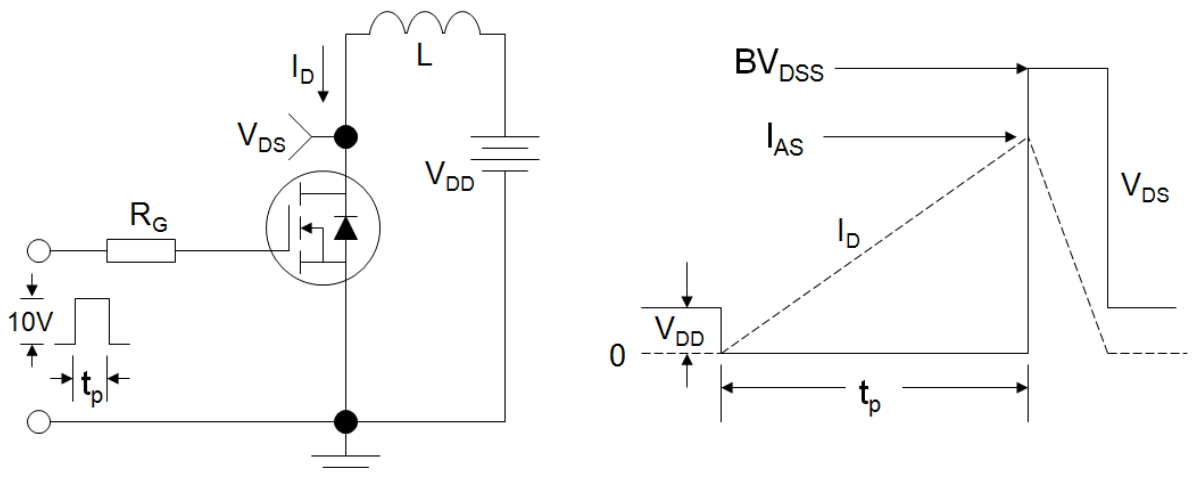
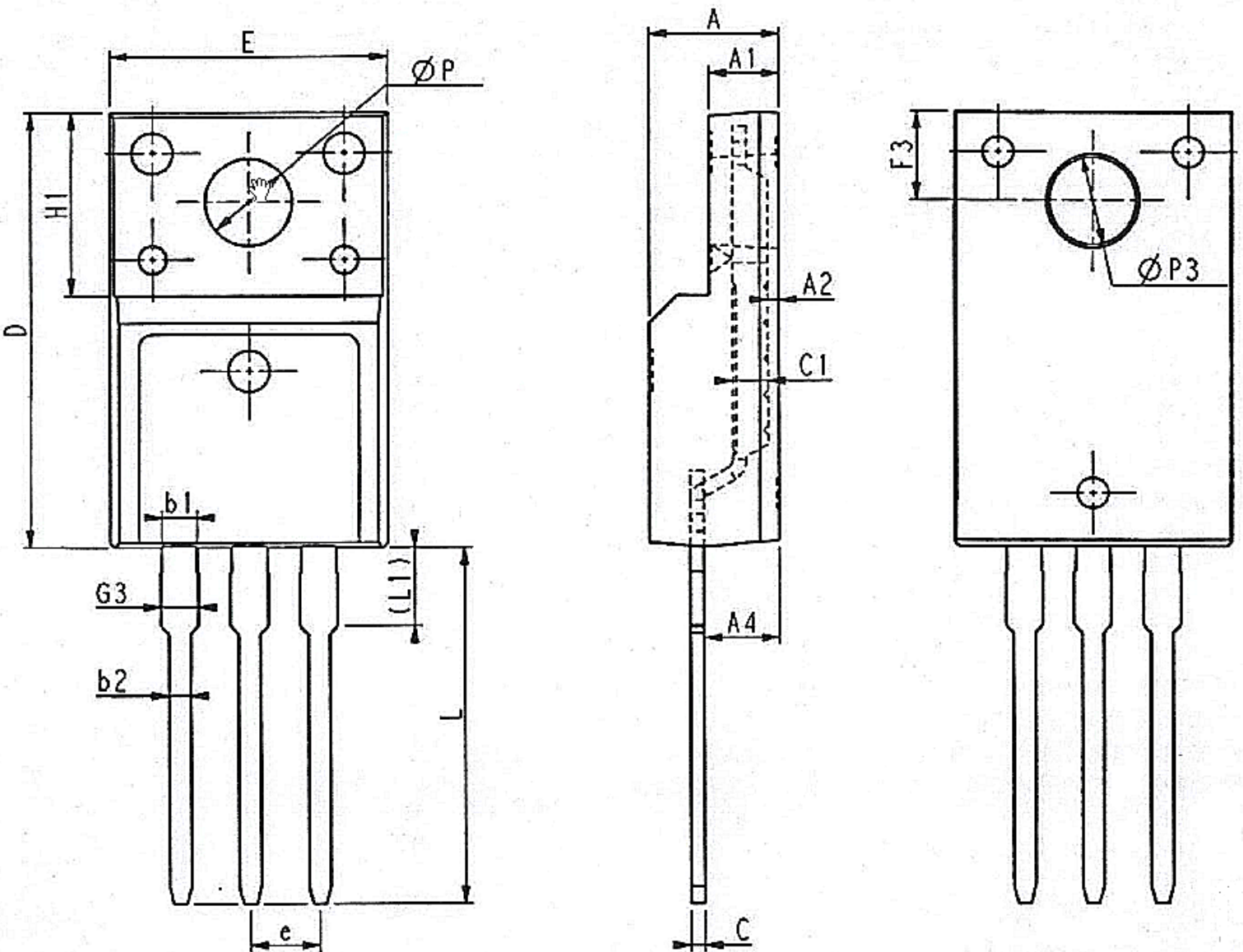


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





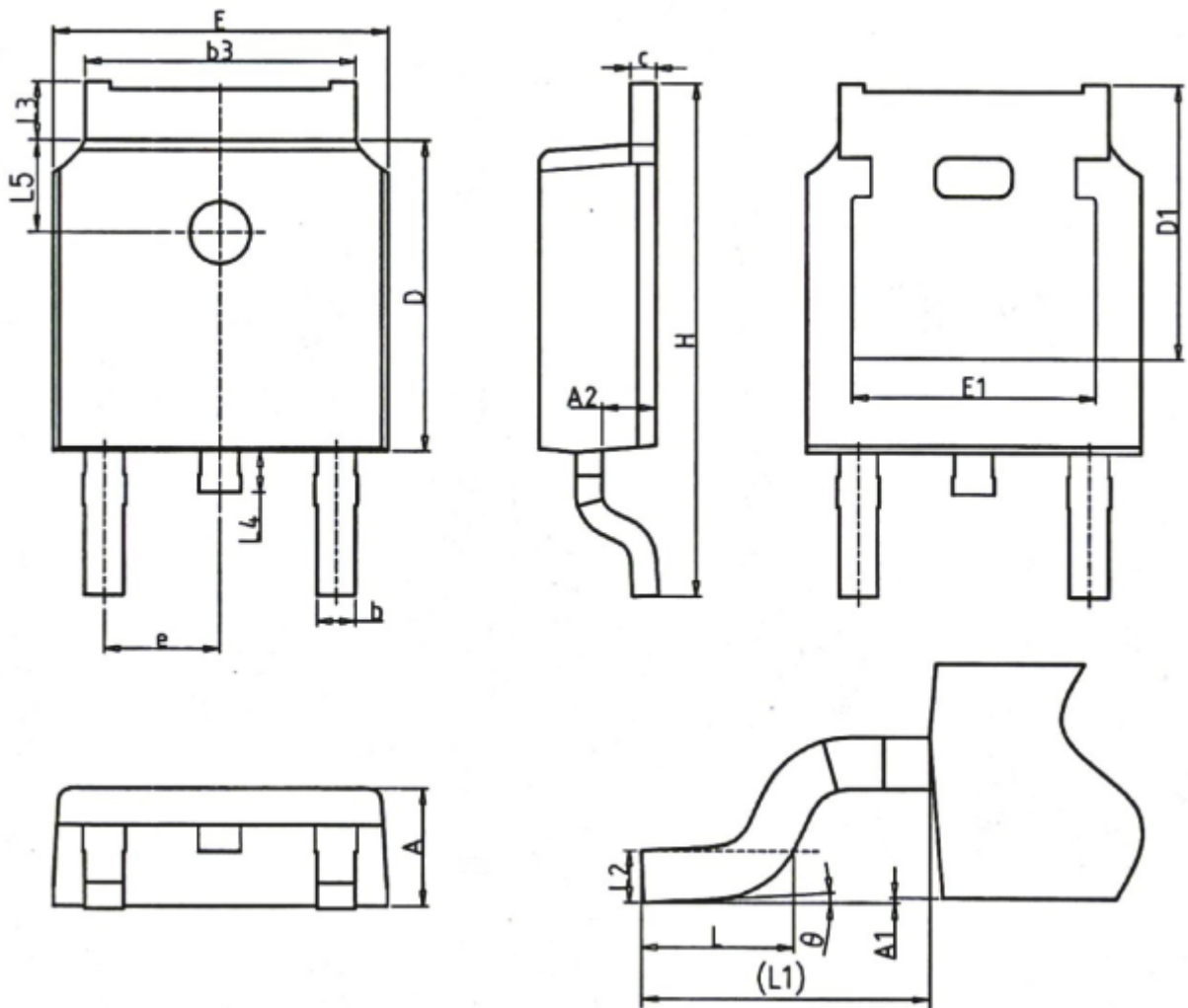
TO-220F



Symbol	Min.	Nom	Max.	Symbol	Min.	Nom	Max.
E	9.96	10.16	10.36	e	2.54BSC		
A	4.50	4.70	4.90	L	12.68	12.98	13.28
A1	2.34	2.54	2.74	L1	2.88	3.03	3.18
A2	0.30	0.45	0.60	ΦP	3.03	3.18	3.38
A4	2.56	2.76	2.96	$\Phi P3$	3.15	3.45	3.65
c	0.40	0.50	0.65	F3	3.15	3.30	3.45
c1	1.20	1.30	1.35	G3	1.25	1.35	1.55
D	15.57	15.87	16.17	b1	1.18	1.28	1.43
H1	6.70REF			b2	0.70	0.80	0.95



TO-252

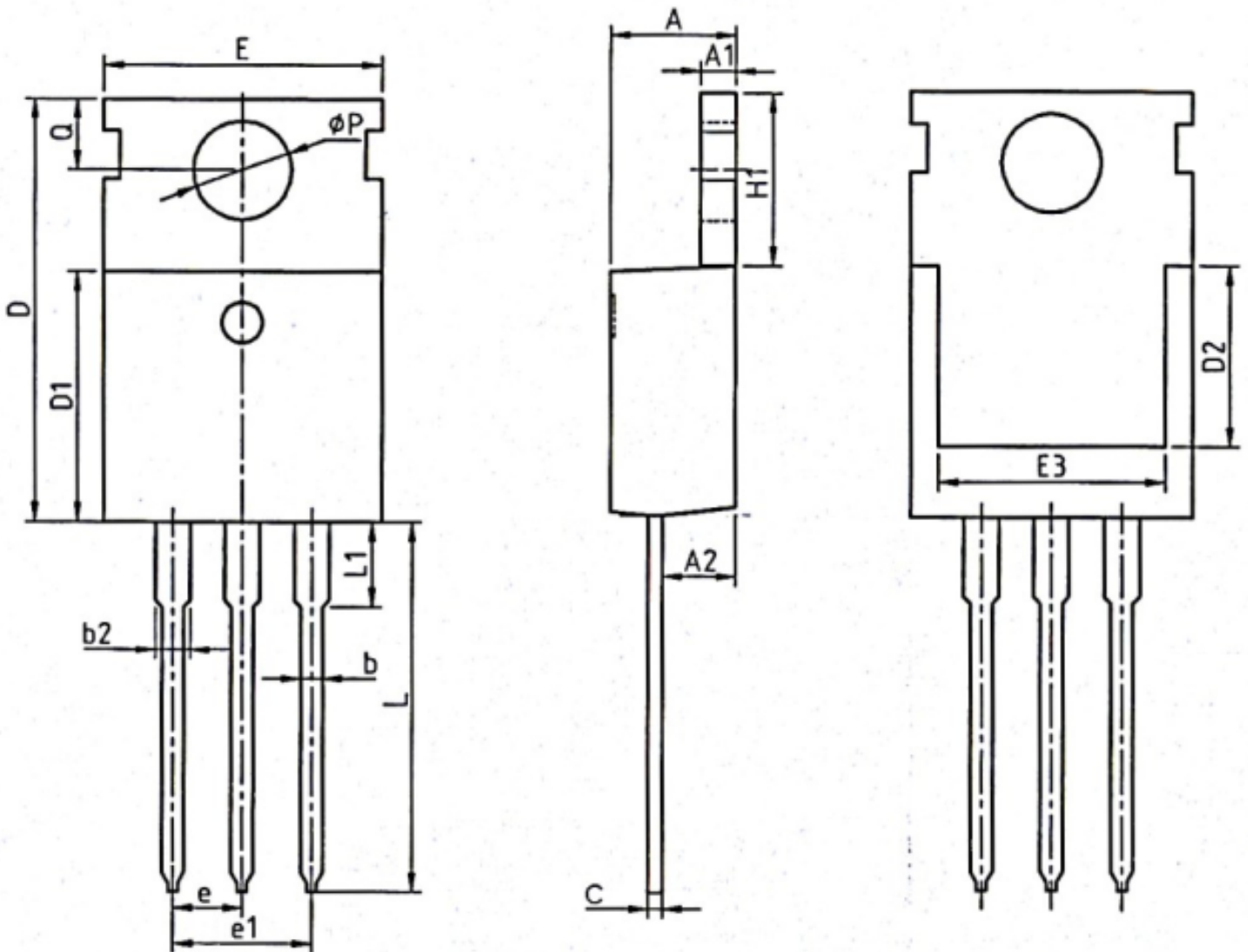


Unit:mm			
Symbol	Min.	Nom	Max.
A	2.20	2.30	2.40
A1	0.00	-	0.20
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b3	5.20	5.33	5.50
c	0.43	0.53	0.63
D	5.98	6.10	6.22
D1	5.30 REF		
E	6.40	6.60	6.80
E1	4.63	-	-

Unit:mm			
Symbol	Min.	Nom	Max.
e	2.286 BSC		
H	9.40	10.10	10.50
L	1.38	1.50	1.75
L1	2.90 REF		
L2	0.51 BSC		
L3	0.88	-	1.28
L4	-	-	1.00
L5	1.65	1.80	1.95
theta	0°	-	8°



TO-220

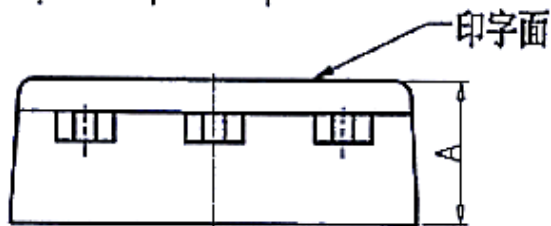
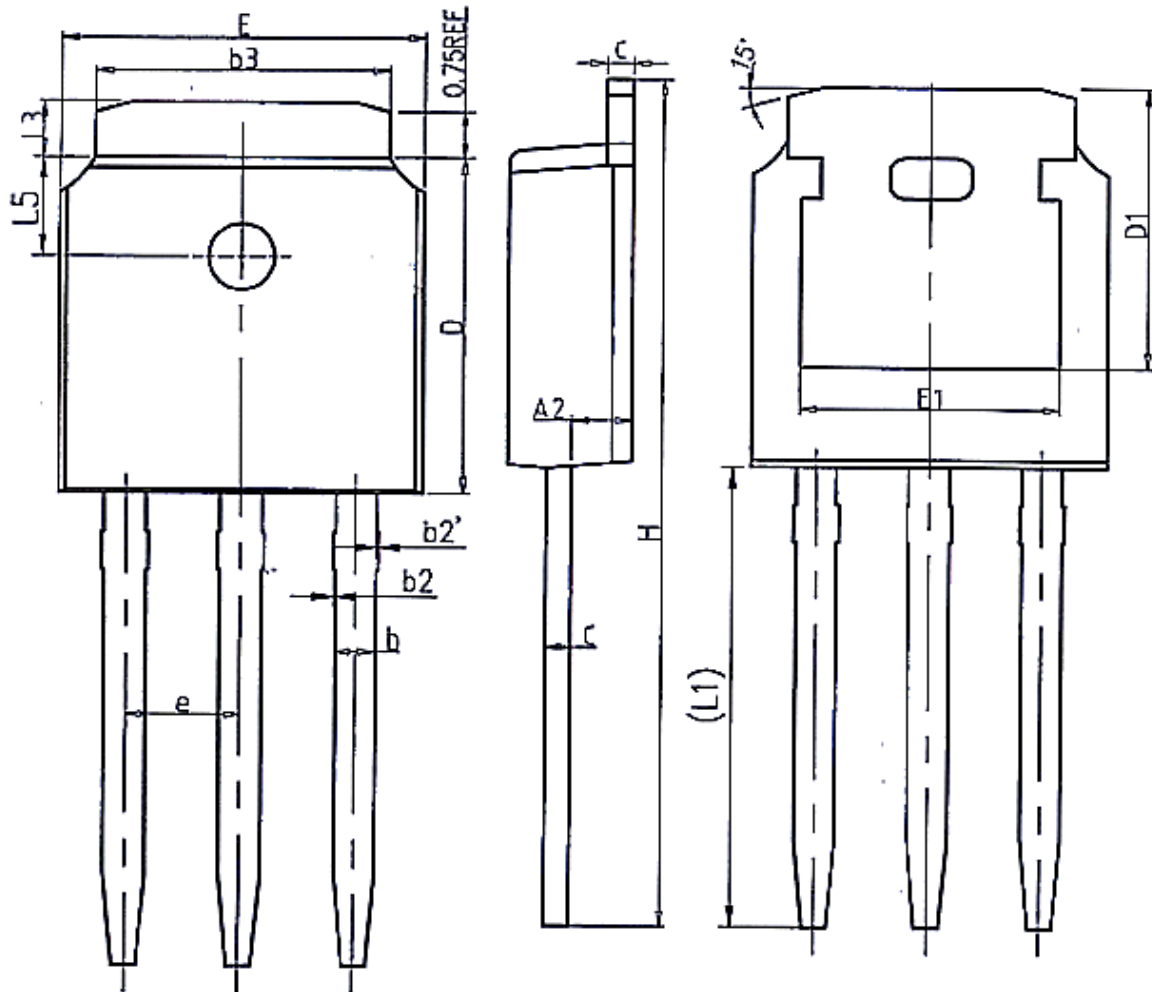


Unit:mm			
Symbol	Min.	Nom	Max.
A	4.37	4.57	4.77
A1	1.25	1.30	1.45
b	2.20	2.40	2.60
b2	1.17	1.27	1.47
c	0.45	0.50	0.60
D	15.10	15.60	16.10
D1	8.80	9.10	9.40
D2	5.50	-	-
E	9.70	10.00	10.30

Unit:mm			
Symbol	Min.	Nom	Max.
E3	7.00	-	-
e	2.54BSC		
e1	5.08BSC		
H1	6.25	6.50	6.85
L	12.75	13.50	13.80
L1	-	3.10	3.40
ΦP	3.40	3.60	3.80
Q	2.60	2.80	3.00



TO-251



Unit:mm			
Symbol	Min.	Nom	Max.
A	2.20	2.30	2.40
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b2	0.00	0.04	0.10
b2'	0.00	0.04	0.10
b3	5.20	5.33	5.50
c	0.43	0.53	0.63
D	5.98	6.10	6.22

Unit:mm			
Symbol	Min.	Nom	Max.
D1	5.30 REF		
E	6.40	6.60	6.80
E1	4.63	-	-
e	2.286 BSC		
H	16.22	16.52	16.82
L1	9.15	9.40	9.65
L3	0.88	1.02	1.28
L5	1.65	1.80	1.95



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